IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1-22. (canceled)

23. (Currently amended) A method for assembling semiconductor devices, comprising:

providing a first semiconductor device;

placing discrete conductive elements over portions of ~~said~~the first semiconductor device; and

positioning a second semiconductor device at least partially over ~~said~~the first semiconductor device, a back side of ~~said~~the second semiconductor device contacting at least some of ~~said~~the discrete conductive elements and being ~~stably~~ supported collectively thereby, ~~said~~the back side and ~~said~~the at least some of ~~said~~the discrete conductive elements being electrically isolated from each other.

24. (Currently amended) The method of claim 23, wherein ~~said~~the positioning ~~said~~the second semiconductor device comprises positioning ~~said~~the second semiconductor device on ~~said~~the at least some of ~~said~~the discrete conductive elements with ~~said~~the back side and ~~said~~the discrete conductive elements in mutual electrical isolation.

25. (Currently amended) The method of claim 24, further comprising:

providing a dielectric coating on at least portions of ~~said~~the discrete conductive elements.

26. (Currently amended) The method of claim 25, wherein ~~said~~the providing comprises forming at least one of a dielectric oxide and a dielectric polymer coating on ~~said~~the at least portions of ~~said~~the discrete conductive elements.

27. (Currently amended) The method of claim 24, wherein ~~said~~the positioning comprises positioning a dielectric layer on at least portions of ~~said~~the back side thereof.

28. (canceled)

29. (Currently amended) The method of claim 23, further comprising:
applying a quantity of adhesive material to at least an active surface of ~~said~~the first semiconductor device.

30. (Currently amended) The method of claim 29, further comprising:
drawing ~~said~~the second semiconductor device toward ~~said~~the first semiconductor device.

31. (Currently amended) The method of claim 30, wherein ~~said~~the drawing is effected by at least one of capillary action of ~~said~~the adhesive material, curing of ~~said~~the adhesive material, application of heat to ~~said~~the adhesive material, and vibration of ~~said~~the adhesive material.

32. (Currently amended) The method of claim 29, wherein ~~said~~the applying includes applying ~~said~~the quantity of adhesive material to ~~said~~the back side of ~~said~~the second semiconductor device.

33. (Currently amended) The method of claim 29, wherein ~~said~~the applying is effected after ~~said~~the positioning ~~said~~the second semiconductor device.

34. (Currently amended) The method of claim 33, further comprising:
drawing ~~said~~the second semiconductor device toward ~~said~~the first semiconductor device.

35. (Currently amended) The method of claim 34, wherein ~~said~~the drawing is effected during curing of ~~said~~the adhesive material.

36. (Currently amended) The method of claim 29, wherein ~~said~~the applying is effected before ~~said~~the positioning ~~said~~the second semiconductor device.

37. (Currently amended) The method of claim 36, further comprising:
biasing at least one of ~~said~~the first and second semiconductor devices toward the other of ~~said~~the first and second semiconductor devices.

38. (Currently amended) The method of claim 37, further comprising:
controlling ~~said~~the biasing.

39. (Currently amended) The method of claim 38, wherein ~~said~~the controlling ~~said~~the biasing comprises controlling biasing force to a level insufficient to deform, kink, bend, or collapse ~~said~~the discrete conductive elements.

40. (Currently amended) The method of claim 23, further comprising:
securing ~~said~~the first semiconductor device and a substrate to one another.

41. (Currently amended) The method of claim 40, wherein ~~said~~the placing discrete conductive elements comprises securing ~~said~~the discrete conductive elements to contact areas of ~~said~~the substrate and bond pads of ~~said~~the first semiconductor device.

42. (Currently amended) The method of claim 41, wherein ~~said~~the securing comprises electrically connecting bond pads of ~~said~~the second semiconductor device to corresponding contact areas of ~~said~~the substrate.

43. (Currently amended) The method of claim 42, further comprising:
encapsulating at least a portion of at least one of ~~said~~the substrate, ~~said~~the first semiconductor device, and ~~said~~the second semiconductor device.

44. (Currently amended) The method of claim 42, further comprising:
forming external conductive elements on ~~said~~the substrate in electrical communication with ~~said~~the corresponding contact areas.

45. (Currently amended) A method for assembling semiconductor devices in a stacked arrangement with the stacked arrangement having a height substantially equal to combined thicknesses of each of the semiconductor devices and distances discrete conductive elements associated therewith protrude above ~~said~~the each of the semiconductor devices, comprising:
providing a first semiconductor device with discrete conductive elements protruding from an active surface thereof; and
positioning a second semiconductor device at least partially over ~~said~~the first semiconductor device and on at least some discrete conductive elements of ~~said~~the discrete conductive elements such that ~~said~~the second semiconductor device is ~~stably~~ supported collectively by ~~said~~the at least some discrete conductive elements and ~~said~~the back side and ~~said~~the at least some ~~said~~ discrete conductive elements are electrically isolated from each other.

46. (Currently amended) The method of claim 45, wherein ~~said~~the positioning comprises positioning ~~said~~the second semiconductor device on ~~said~~the at least some of ~~said~~the discrete conductive elements with a back side of ~~said~~the second semiconductor device electrically isolated from ~~said~~the discrete conductive elements.

47. (Currently amended) The method of claim 46, further comprising:

providing a dielectric coating on at least portions of ~~said~~the at least some of ~~said~~the discrete conductive elements.

48. (Currently amended) The method of claim 46, wherein ~~said~~the positioning comprises positioning a second semiconductor device that includes a dielectric coating on at least portions of ~~said~~the back side thereof.

49. (Currently amended) The method of claim 45, further comprising:

applying a quantity of adhesive material at least to ~~said~~the active surface of ~~said~~the first semiconductor device.

50. (Currently amended) The method of claim 49, further comprising:

drawing ~~said~~the second semiconductor device toward ~~said~~the first semiconductor device.

51. (Currently amended) The method of claim 50, wherein ~~said~~the drawing is effected by at least one of capillary action of ~~said~~the adhesive material, curing of ~~said~~the adhesive material, application of heat to ~~said~~the adhesive material, and vibration of ~~said~~the adhesive material.

52. (Currently amended) The method of claim 49, wherein ~~said~~the applying is effected before ~~said~~the positioning.

53. (Currently amended) The method of claim 49, wherein ~~said~~the applying is effected after ~~said~~the positioning.

54. (Currently amended) The method of claim 53, further comprising:

drawing ~~said~~the second semiconductor device toward ~~said~~the first semiconductor device.

55. (Currently amended) The method of claim 54, wherein ~~said~~the drawing is effected during curing of ~~said~~the adhesive material.

56. (Currently amended) The method of claim 49, further comprising:
biasing at least one of ~~said~~the first and second semiconductor devices toward the other of ~~said~~the first and second semiconductor devices.

57. (Currently amended) The method of claim 56, further comprising:
controlling ~~said~~the biasing.

58. (Currently amended) The method of claim 57, wherein ~~said~~the controlling ~~said~~the biasing comprises controlling biasing force to a level insufficient to deform, kink, bend, or collapse ~~said~~the discrete conductive elements.

59. (Currently amended) The method of claim 45, further comprising:
positioning ~~said~~the first semiconductor device relative to a substrate.

60. (Currently amended) The method of claim 59, further comprising:
connecting ~~said~~the discrete conductive elements to corresponding contact areas of ~~said~~the substrate.

61. (Currently amended) The method of claim 59, further comprising:
establishing electrical communication between bond pads of ~~said~~the second semiconductor device and corresponding contact areas of ~~said~~the substrate.

62. (Currently amended) The method of claim 61, wherein ~~said~~the establishing communication comprises:

placing additional discrete conductive elements between each of ~~said~~the bond pads and a corresponding contact area of ~~said~~the corresponding contact areas.

63. (Currently amended) The method of claim 46, further comprising:
providing at least one external connective element in communication with at least one bond pad of each of ~~said~~the first and second semiconductor devices.

64. (Currently amended) The method of claim 63, further comprising:
encapsulating at least portions of ~~said~~the first and second semiconductor devices.

65-69. (canceled)